

LBSS138WT1G

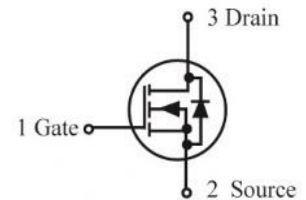
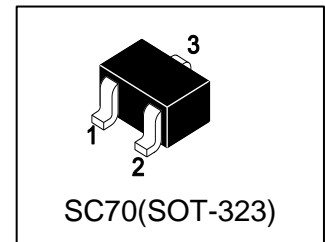
S-LBSS138WT1G

Power MOSFET

200 mAmps, 50 Volts N-Channel SC-70

1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- Low threshold voltage ($V_{GS(th)}$: 0.5V...1.5V) makes it ideal for low voltage applications.



2. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
LBSS138WT1G	J1	3000/Tape&Reel
LBSS138WT3G	J1	10000/Tape&Reel

3. MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	VDSS	50	Vdc
Gate-to-Source Voltage – Continuous	VGS	± 20	Vdc
Drain Current			mAdc
– Continuous $T_A = 25^\circ\text{C}$	ID	200	
– Pulsed ($t_p \leq 10\mu\text{s}$)	IDM	800	

4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-5 Board (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	PD	150	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient(Note 1)	ROJA	556	$^\circ\text{C}/\text{W}$
Junction and Storage temperature	T_J, T_{stg}	$-55 \sim +150$	$^\circ\text{C}$
Maximum Lead Temperature for Solde Purposes, for 10 seconds	TL	260	$^\circ\text{C}$

1. FR-5 = 1.0×0.75×0.062 in.

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)
OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain–Source Breakdown Voltage (VGS = 0, ID = 250μAdc)	VBRDSS	50	-	-	Vdc
Zero Gate Voltage Drain Current (VGS = 0, VDS = 25 Vdc) (VGS = 0, VDS = 50 Vdc)	IDSS	- -	- -	0.1 0.5	μAdc
Gate–Body Leakage Current, Forward (VGS = 20 Vdc)	IGSSF	-	-	0.1	μAdc
Gate–Body Leakage Current, Reverse (VGS = - 20 Vdc)	IGSSR	-	-	-0.1	μAdc

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage (VDS = VGS, ID = 1.0mAdc)	VGS(th)	0.5	-	1.5	Vdc
Static Drain–Source On–State Resistance (VGS = 2.75 Vdc, ID < 200 mAdc, TA = -40°C to +85°C) (VGS = 5.0 Vdc, ID = 200 mAdc)	RDS(on)	- -	5.6 -	10 3.5	Ohms
Forward Transconductance (VDS = 25 Vdc, ID = 200 mAdc, f = 1.0 kHz)	gfs	100	-	-	mS

DYNAMIC CHARACTERISTICS

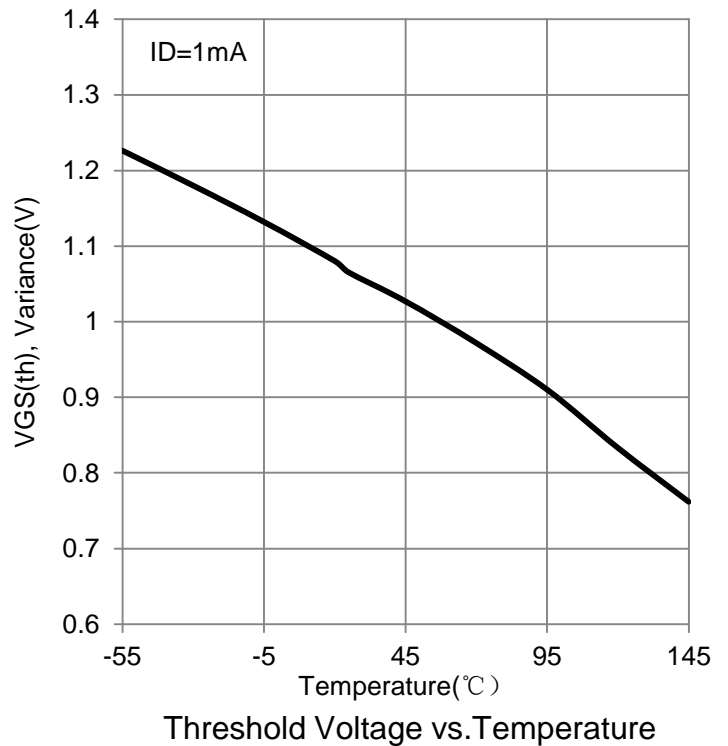
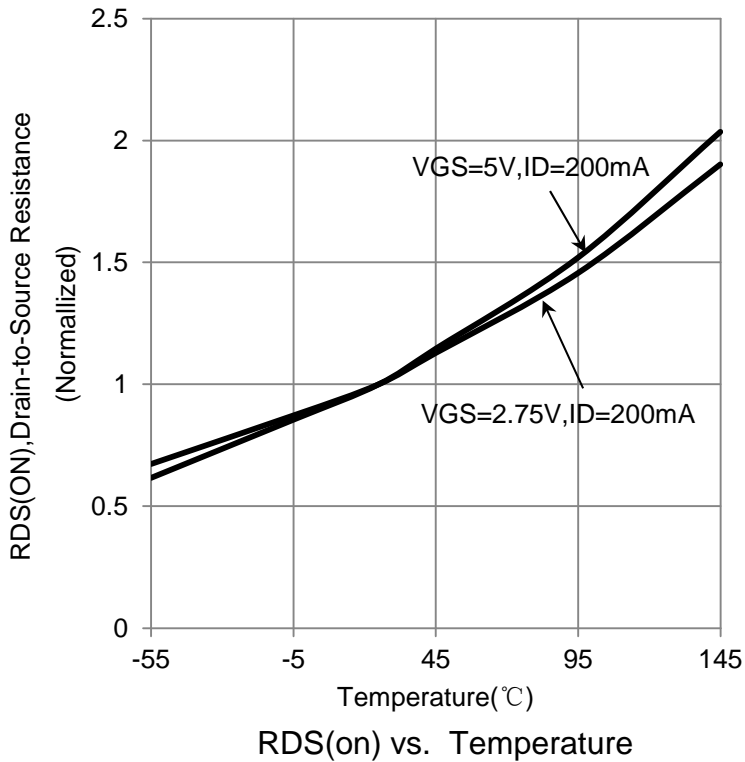
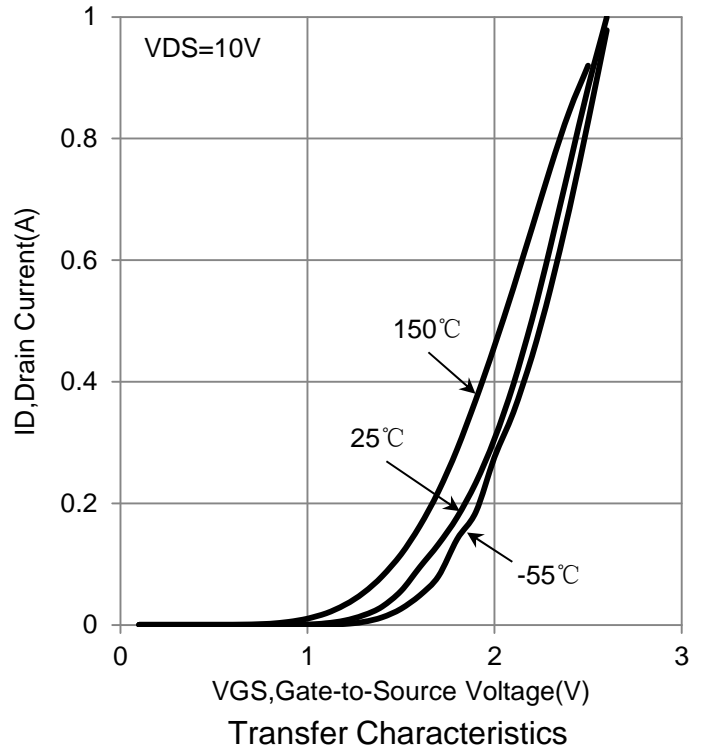
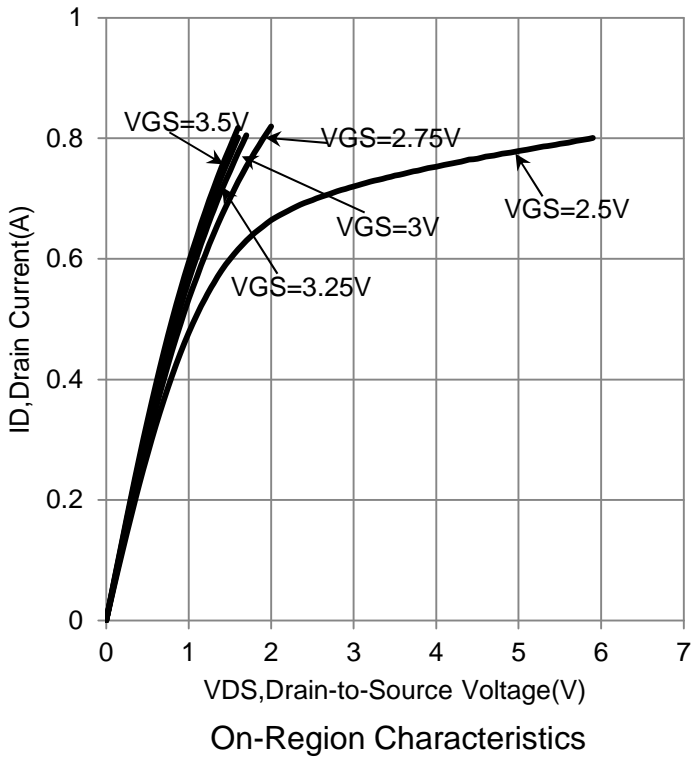
Input Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Ciss	-	40	50	pF
Output Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Coss	-	12	25	pF
Reverse Transfer Capacitance (VDS = 25 Vdc, VGS = 0, f = 1.0 MHz)	Ciss	-	3.5	5.0	pF

SWITCHING CHARACTERISTICS

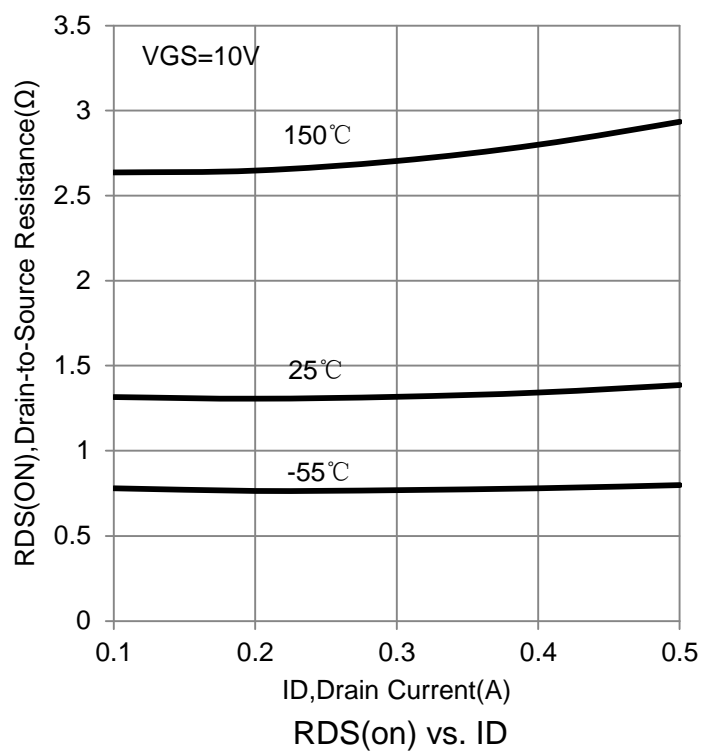
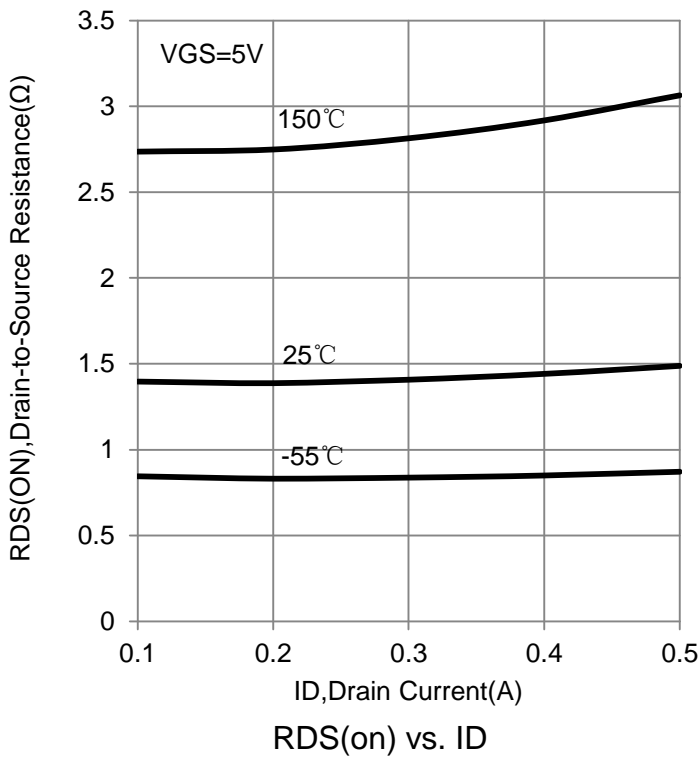
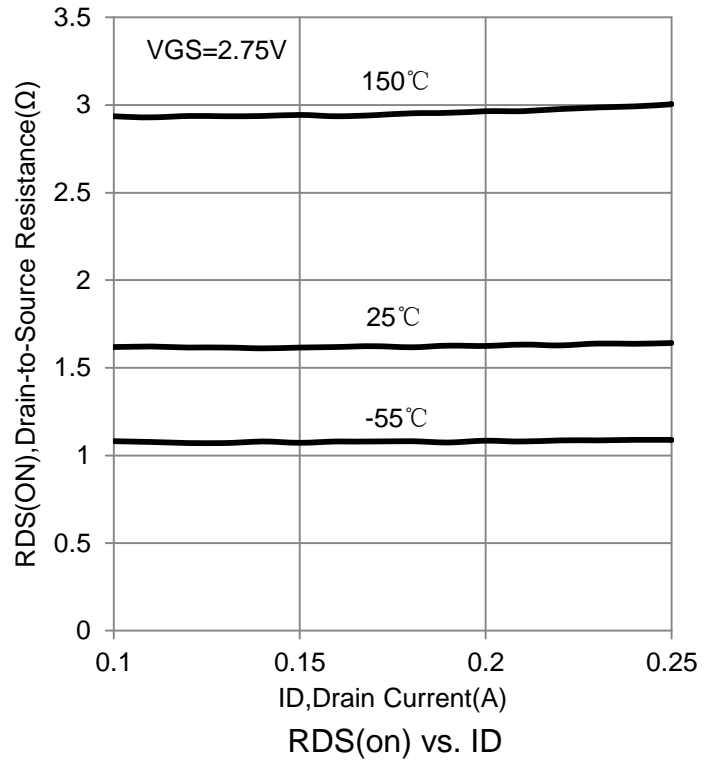
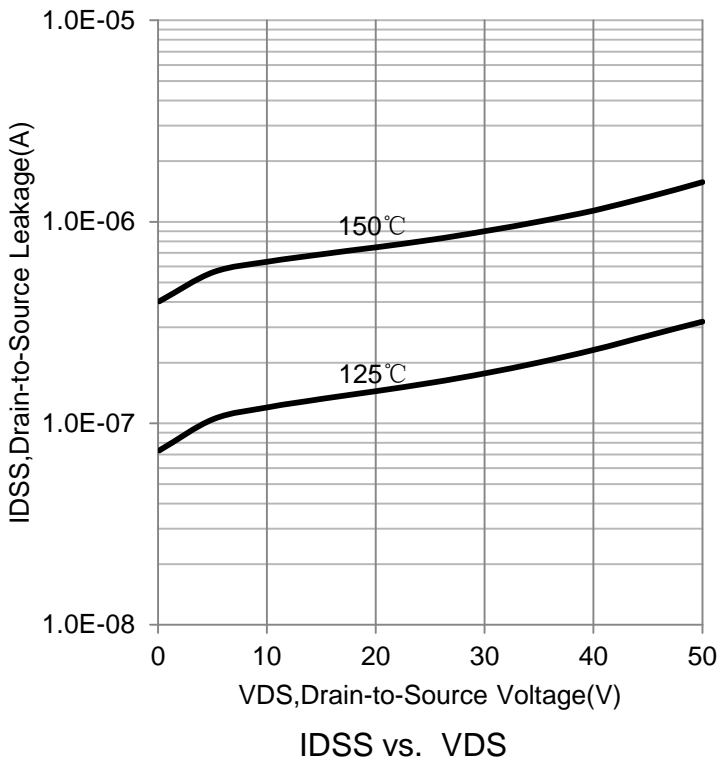
Turn-On Delay Time	(VDD = 30 Vdc , ID =200 mAdc)	td(on)	-	-	20	ns
Turn-Off Delay Time		td(off)	-	-	20	

2.Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$.

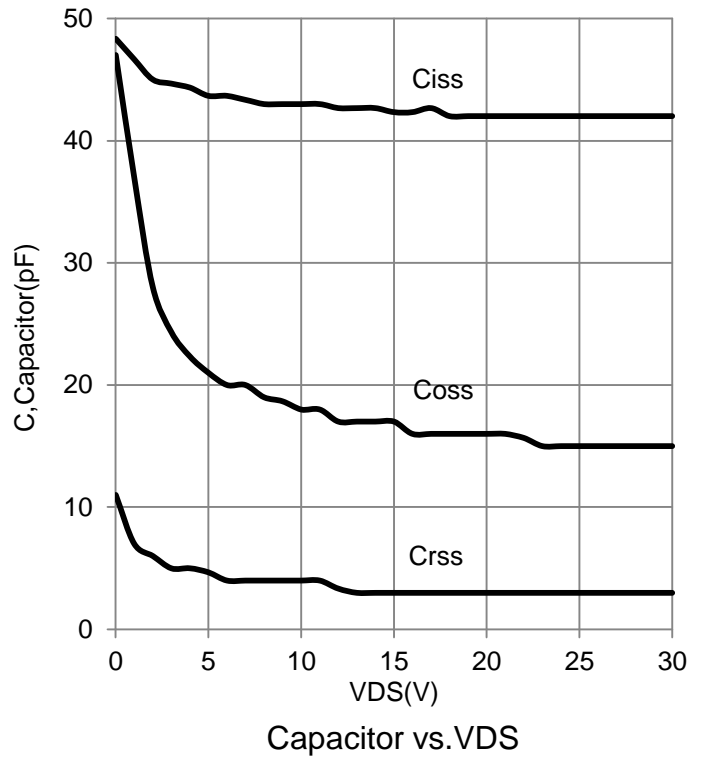
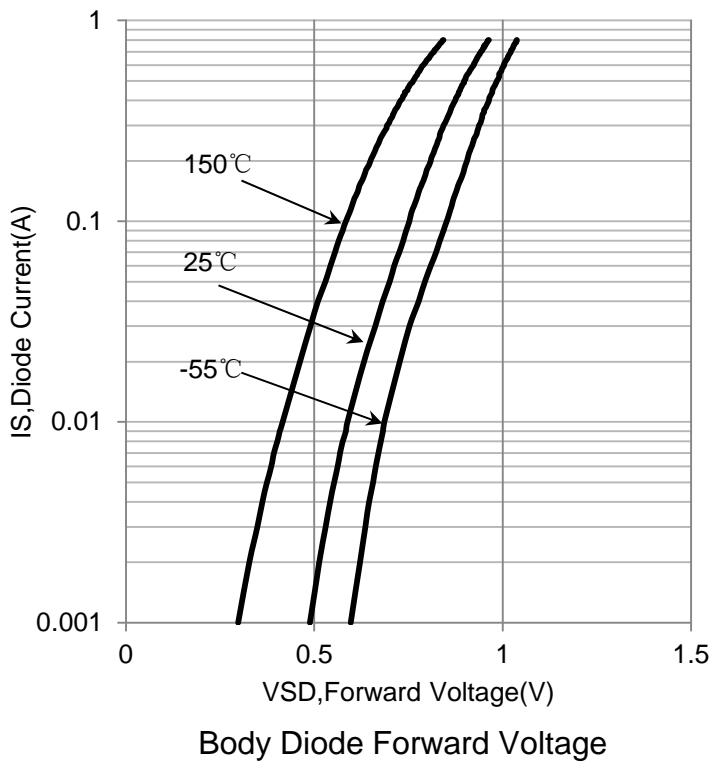
6. ELECTRICAL CHARACTERISTICS CURVES



6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



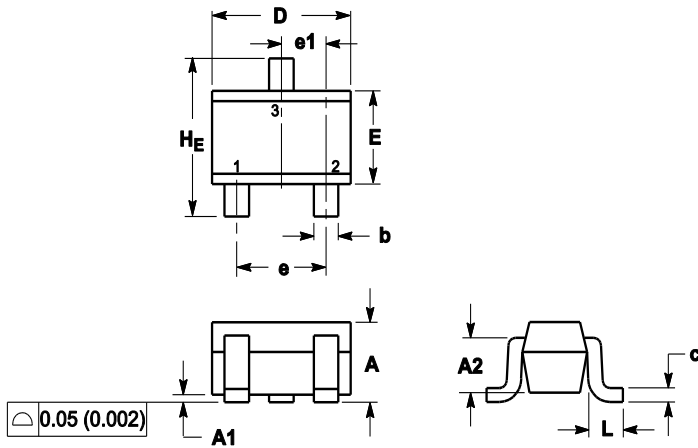
6.ELECTRICAL CHARACTERISTICS CURVES(Con.)



7. OUTLINE AND DIMENSIONS

Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.039
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70REF			0.028REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65REF			0.026REF		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

8. SOLDERING FOOTPRINT

